

REMARKS/ARGUMENTS

Favorable reconsideration of this application as presently amended and in light of the following discussion is respectfully requested.

After entry of the foregoing amendment, Claims 6 and 22-26 are pending in the present application. Claims 1 and 7 have been canceled without prejudice or disclaimer, Claims 6 and 22 have been rewritten in independent form, and Claims 23-26 are added by the present amendment. Support for new Claims 23-26 can be found in the claims and specification as originally filed. No new matter has been added.

In the outstanding Office Action, Claim 1 was rejected under 35 U.S.C. § 102(e) as anticipated by U.S. Publication No. 2003/0209774 to Jimbo et al. (herein "Jimbo"); and Claim 7 was rejected under 35 U.S.C. § 103(a) as unpatentable over Jimbo.

Applicants thank the Examiner for the indication of allowable subject matter. In light of this indication, Claims 6 and 22 have been placed in independent form. Accordingly, Applicants submit that Claims 6 and 22 are now in condition for allowance.

While Claims 1 and 7 have been cancelled, Applicants will treat the rejections applied to these claims in the Official Action of June 28, 2005 as if they were applied to new Claims 23-26.

Applicants' new independent Claim 23 is directed to a semiconductor device. A ring region is formed of a diffused region of a second conductivity type and is formed within the major surface of the first base region between the second base region and the stopper region.

Jimbo describes a semiconductor device with a spiral thin film layer (6) located on the front surface of a substrate (10).¹ The spiral thin film layer (6) is composed of alternating

¹ Jimbo at ¶ 0084.

first conductivity type film layer (4) and second conductivity type film layer (5).² Moreover, the spiral thin film layer (6) if formed through a dielectric oxide film (18).³

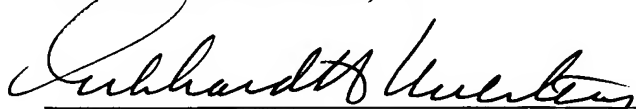
Conversely, in an exemplary embodiment of the Applicants' invention as recited in Claim 23, a ring region is formed of a diffused region of a second conductivity type and is formed within the major surface of the first base region between the second base region and the stopper region. This claimed feature results in easier adjustment to the diffused layer resistance of the ring region, allowing uniform dispersion of electric field distribution.⁴

Jimbo does not disclose or suggest a ring region formed of a diffused region of a second conductivity type and formed within the major surface of the first base region between the second base region and the stopper region as recited in new independent Claim 23 or any claim depending therefrom.

Consequently, in light of the above discussion and in view of the present amendment, the present application is believed to be in condition for allowance and an early and favorable action to that effect is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.



Eckhard H. Kuesters
Attorney of Record
Registration No. 28,870

Customer Number

22850

Tel: (703) 413-3000

Fax: (703) 413 -2220

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² Jimbo at ¶ 0083.

³ Jimbo at ¶ 0084.

⁴ Specification at page 7.